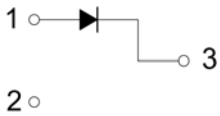
CMPSH-3/-3A/-3C/-3S

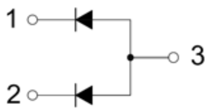
SCHOTTKY BARRIER DIODE

FEATURES

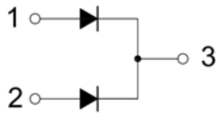
- High Switching Speed
- Low Forward Voltage



CMPSH-3



CMPSH-3A



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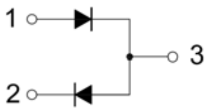


CMPSH-3S

SOT-23-3

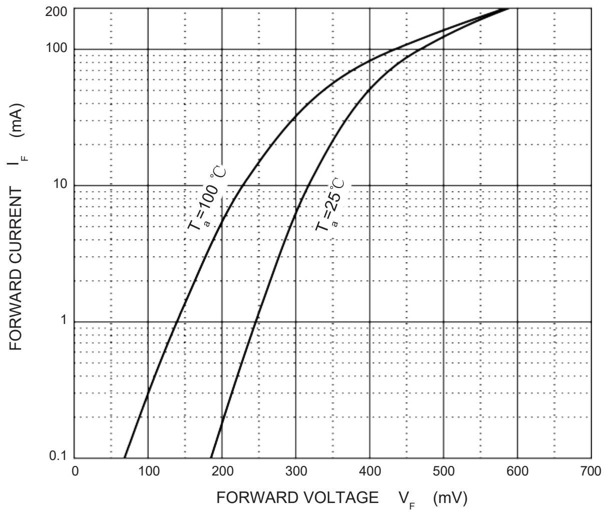
MAXIMUM RATINGS (T_a=25℃ unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{RRM}	Peak Repetitive Reverse Voltage	30	V
I_O	Continuous Forward Current	100	mA
I_{FRM}	Peak Repetitive Forward Current	350	mA
I_{FSM}	Non-repetitive Peak Forward Surge Current @ t=8.3ms	750	mA
P_D	Power Dissipation	350	mW
$R_{\theta JA}$	Thermal Resistance from Junction to Ambient	286	℃/W
T_j	Operating Junction Temperature Range	-40~+125	℃
T_{stg}	Storage Temperature Range	-55~+150	℃

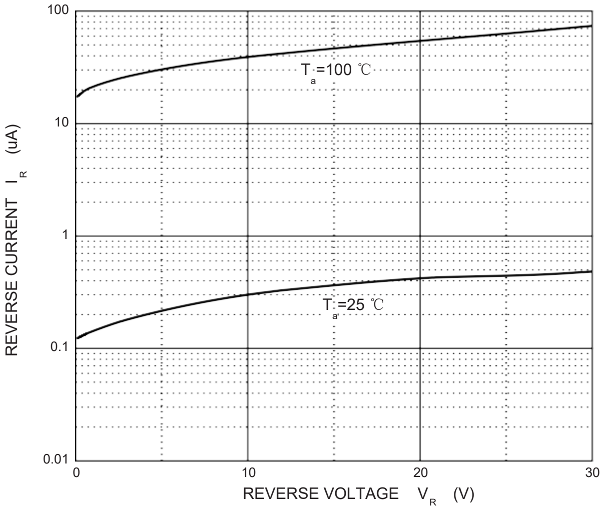
ELECTRICAL CHARACTERISTICS(T_a=25℃ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Reverse voltage	$V_{(BR)}$	I_R=100μA	30			V
Reverse current	I_R	V_R=25V			0.5	μA
Forward voltage	V_F	I_F=2mA			0.33	V
		I_F=15mA			0.45	
		I_F=100mA			1	
Total capacitance	C_{tot}	V_R=1V,f=1MHz		7		pF
Reverse recovery time	t_{rr}	I_F= I_R=10mA, I_{rr}=0.1×I_R, R_L=100Ω		5		ns

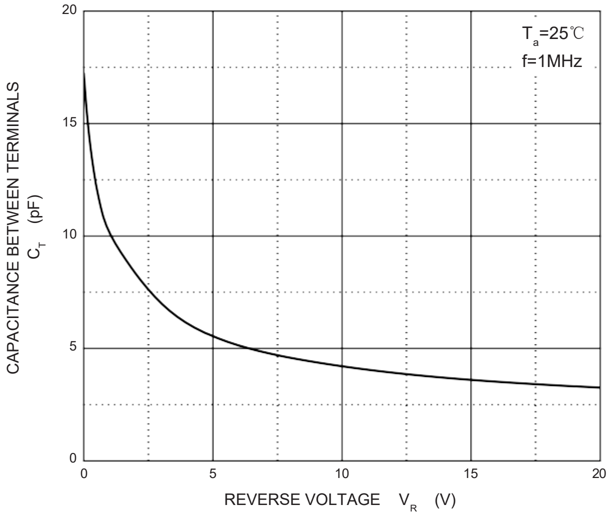
Forward Characteristics



Reverse Characteristics



Capacitance Characteristics



Power Derating Curve